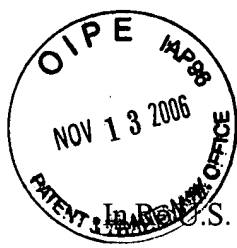


ITJ -

PATENT



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Reply, Please Refer to U.S. Patent Application

Applicant: Masahiko Ando et al.

Serial No.: 10/500,268

Filed: June 23, 2004

For: **Method For Eliminating Defects From
Single Crystal Silicon, And Single
Crystal Silicon**

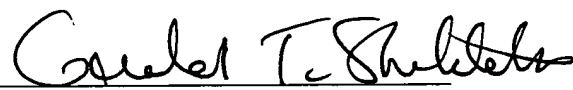
Examiner: Felisa Carla Hiteshew

Art Unit: 1722

)
) Confirmation No.: 9828
)

) *I hereby certify that this correspondence is*
) *being deposited with the United Postal Service*
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) *Mail Stop AMENDMENT, Commissioner of*
) *Patents, P.O. Box 1450, Alexandria, VA, 22313-*
) *1450, on*

) November 8, 2006
)

) 
) Gerald T. Shekleton Reg. No. 27,466
)
)

AMENDMENT

Mail Stop AMENDMENT
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

The Office Action of August 8, 2006 has been carefully reviewed and the following
amendments and remarks are made in response thereto.